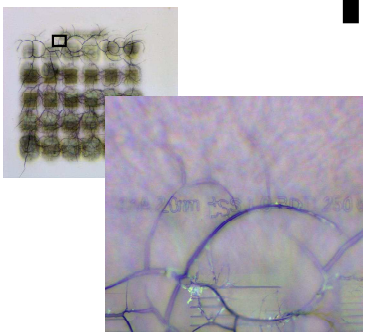
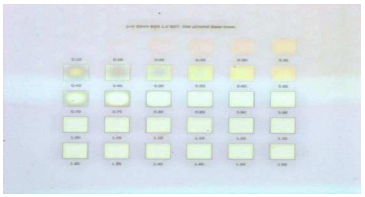
DisChem
CHEMISTRY FOR ADVANCED LITHOGRAPHY

DisCharge

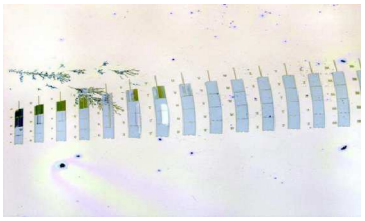
ELECTRON BEAM LITHOGRAPHY ANTI-CHARGING AGENT



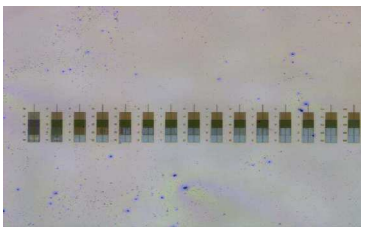
300 nm PMMA 950 A4 / PDMS on bulk Si without charge dissipation agent. Sudden charge accumulation and dielectric breakdown of PDMS resulting in significant cracking of the resist.



WITH DisCharge: no charge accumulation. Structure appears as expected with no harm to PDMS.



300 nm ZEP520A on fused silica without charge dissipation agent. Poor shape fidelity of the tower pattern.



WITH DisCharge: no charge accumulation. Tower pattern appears as expected

DisCharge *Advantage in Electron Beam Lithography*

- Efficient charge dissipation in electron beam lithography (EBL) on a broad range of resist materials (novalac resist, PMMA, HSQ, mr-PosEBR, CSAR 62, ZEP520A, HSQ)
- Improved shape fidelity and positional accuracy for EBL resist patterning on insulating substrates such as fused silica, quartz, glass, PDMS, etc.
- Water based formulation with excellent wetting properties. Simple spin coat application provides 40 nm conductive film at 1000 RPM.
- Easy residue free removal by water or IPA rinse.
- Competitively priced. Ideal for both research and industrial applications.
- Two-year shelf life at room temperature. Highly stable permanently charged non-polymer formulation. No filtration required prior to use.

Please contact us to receive additional product information and no-charge product samples for evaluation.

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